



# 1A, LI-ION, LI-POL BATTERY CHARGER WITH ADJUSTABLE BATTERY VOLTAGE

#### **FEATURES**

- Pin Select Battery Voltage (4.06V/4.2V)
- Integrated Power FET and Current Sensor for Up to 1A Charge Applications From AC Adapter
- Precharge Conditioning With Safety Timer
- Charge and Power-Good Status Output
- Automatic Sleep Mode for Low Power Consumption
- Integrated Charge-Current Monitor
- Fixed 7-Hour Fast Charge Safety Timer
- Ideal for Low-Dropout Charger Designs for Single-Cell Li-lon or Li-Pol Packs in Space-Limited Portable Applications
- Small 3-mm × 3-mm SON Package

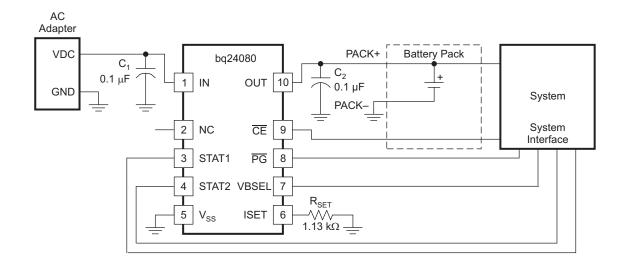
### **APPLICATIONS**

- PDAs, MP3 Players
- Digital Cameras
- Internet Appliances
- Smartphones

#### DESCRIPTION

The bq24083 is highly integrated and flexible Li-Ion linear charge device targeted at space-limited charger applications. It offers an integrated power FET and current sensor, high-accuracy current and voltage regulation, charge status, and charge termination, in a single monolithic device. An external resistor sets the magnitude of the charge current. The bq24083 has an option of two output battery charge voltages: 4.06 V and 4.2 V.

The device charges the battery in three phases: conditioning, constant current, and constant voltage. Charge is terminated based on minimum current. An internal charge timer provides a backup safety for charge termination. The device automatically restarts the charge if the battery voltage falls below an internal threshold. The device automatically enters sleep mode when the ac adapter is removed.



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### **ORDERING INFORMATION**

TJ	CHARGE REGULATION VOLTAGE (V)	FUNCTIONS	FAST-CHARGE TIMER (HOURS)	PART NUMBER <sup>(1)(2)</sup>	MARKINGS
40°C to 105°C	4.2/ 4.06	CE, PG, and VBSEL	7	bq24083DRCT	CFZ
–40°C to 125°C	4.2/ 4.06	CE, PG, and VBSEL	/	bq24083DRCR	GFZ

1) The DRC package is available taped and reeled only in quantities of 3,000 devices per reel.

#### **DISSIPATION RATINGS**

PACKAGE	$R_{ heta JA}$	$R_{ heta JC}$	T <sub>A</sub> < 40°C POWER RATING	DERATING FACTOR ABOVE T <sub>A</sub> = 40°C
DRC <sup>(1)</sup>	46.87 °C/W	4.95 °C/W	1.5 W	0.021 W/°C

This data is based on using the JEDEC High-K board and the exposed die pad is connected to a copper pad on the board. This is connected to the ground plane by a 2- x 3-via matrix.

#### **ABSOLUTE MAXIMUM RATINGS**

over operating free-air temperature range unless otherwise noted(1)

			VALUE	UNIT
VI	Input voltage (2)	IN, $\overline{\text{CE}}$ , ISET, OUT, $\overline{\text{PG}}$ , STAT1, STAT2, VBSEL	–0.3 to 7	V
	Output sink/source current	STAT1, STAT2, PG	15	mA
	Output current	OUT	1.5	Α
T <sub>A</sub>	Operating free-air temperature r	ange	40 to 10F	°C
TJ	Junction temperature range		-40 to 125	°C
T <sub>stg</sub>	Storage temperature		-65 to 150	°C

<sup>(1)</sup> Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

### RECOMMENDED OPERATING CONDITIONS

		MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage	4.5	6.5	V
$T_{J}$	Operating junction temperature range	0	125	°C

<sup>(2)</sup> For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI Web site at www.ti.com.

<sup>(2)</sup> All voltages are with respect to V<sub>SS</sub>.



### **ELECTRICAL CHARACTERISTICS**

over  $0^{\circ}C \le T_{J} \le 125^{\circ}C$  and recommended supply voltage (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
INPUT CUI	RRENT					
I <sub>CC(VCC)</sub>	V <sub>CC</sub> current	$V_{CC} > V_{CC(min)}$		1.2	2	mA
I <sub>CC(SLP)</sub>	Sleep current	Sum of currents into OUT pin, V <sub>CC</sub> < V <sub>(SLP)</sub>		2	5	
CC(STBY)	Standby current	CE = High, 0°C ≤ T <sub>J</sub> ≤ 85°C			150	μΑ
I <sub>IB(OUT)</sub>	Input current on OUT pin	Charge DONE, V <sub>CC</sub> > V <sub>CC(MIN)</sub>		1	5	
/OLTAGE	REGULATION V <sub>O(REG)</sub> + V <sub>(DO-MAX)</sub> ≤ V <sub>CC</sub> , I	(TERM) < I <sub>O(OUT)</sub> ≤ 1 A			·	
.,	0	VBSEL = HI		4.06		.,
$V_{O(REG)}$	Output voltage	VBSEL = LO		4.2		V
	Nalla and an Indian	T <sub>A</sub> = 25°C	-0.35%		0.35%	
	Voltage regulation accuracy		-1%		1%	
V <sub>(DO)</sub>	Dropout voltage (V <sub>(IN)</sub> - V <sub>(OUT)</sub> )	$V_{O(OUT)} = V_{O(REG)}, I_{O(OUT)} = 1 \text{ A}$ $V_{O(REG)} + V_{(DO)}) \le V_{CC}$		350	500	mV
CURRENT	REGULATION				-	
I <sub>O(OUT)</sub>	Output current range <sup>(1)</sup>	$V_{I(OUT)} > V_{(LOWV)},$ $V_{I(IN)} - V_{I(OUT)} > V_{(DO)}, V_{CC} \ge 4.5 \text{ V}$	50		1000	mA
V <sub>(SET)</sub>	Output current set voltage	$ \begin{array}{l} \mbox{Voltage on ISET pin, $V_{CC} \geq 4.5$ V,} \\ \mbox{$V_{I} \geq 4.5$ V, $V_{I(OUT)} > V_{(LOWV)},$} \\ \mbox{$V_{I} - V_{I(OUT)} > V_{(DO)}$} \end{array} $	2.463 2.5		2.538	V
		50 mA ≤ I <sub>O(OUT)</sub> ≤ 1 A	307	322	337	
K <sub>(SET)</sub>	Output current set factor	10 mA ≤ I <sub>O(OUT)</sub> < 50 mA	296	320	346	
		1 mA ≤ I <sub>O(OUT)</sub> < 10 mA	246	320	416	
PRECHAR	GE AND SHORT-CIRCUIT CURRENT REG	ULATION			-	
$V_{(LOWV)}$	Precharge to fast-charge transition threshold	Voltage on OUT pin	2.8	3	3.2	٧
	Deglitch time for fast-charge to precharge transition	$V_{CC(MIN)} \ge 4.5 \text{ V}, t_{FALL} = 100 \text{ ns}, \\ 10\text{-mV overdrive}, \\ V_{I(OUT)} \text{ decreasing below threshold}$	250	375	500	ms
O(PRECHG)	Precharge range (2)	$0 \text{ V} < V_{I(OUT)} < V_{(LOWV)}, t < t_{(PRECHG)}$	5		100	mA
V <sub>(PRECHG)</sub>	Precharge set voltage	Voltage on ISET pin, $V_{O(REG)} = 4.2 \text{ V}$ , $0 \text{ V} < V_{I(OUT)} > V_{(LOWV)}$ , $t < t_{(PRECHG)}$	240	255	270	mV
ΓERMINAT	ION DETECTION				·	
(TERM)	Charge termination detection range (3)	$V_{I(OUT)} > V_{(RCH)}, t < t_{(TRMDET)}$	5		100	mA
V <sub>(TERM)</sub>	Charge termination detection set voltage	$ \begin{aligned} & \text{Voltage on ISET pin, V}_{O(REG)} = 4.2 \text{ V,} \\ & \text{V}_{I(OUT)} > \text{V}_{(RCH)}, \text{ t} < \text{t}_{(TRMDET)} \end{aligned} $	235	250	265	mV
t <sub>TRMDET</sub>	Deglitch time for termination detection	V <sub>CC(MIN)</sub> ≥ 4.5 V, t <sub>FALL</sub> = 100 ns charging current decreasing below 10-mV overdrive	250	375	500	ms

See Equation 2 in the Function Description section.
 See Equation 1 in the Function Description section.
 See Equation 4 in the Function Description section.



# **ELECTRICAL CHARACTERISTICS (continued)**

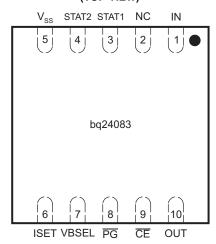
over  $0^{\circ}C \le T_{J} \le 125^{\circ}C$  and recommended supply voltage (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
BATTERY	RECHARGE THRESHOLD		<u>.</u>			
V <sub>(RCH)</sub>	Recharge threshold		V <sub>O(REG)</sub> - 0.115	V <sub>O(REG)</sub> - 0.10	V <sub>O(REG)</sub> - 0.085	V
t <sub>(DEGL)</sub>	Deglitch time for recharge detect	V <sub>CC(MIN)</sub> ≥ 4.5 V, t <sub>FALL</sub> = 100 ns decreasing below or increasing above threshold, 10-mV overdrive	250	375	500	ms
STAT1, ST	AT2, and PG OUTPUTS					
V <sub>OL</sub>	Low-level output saturation voltage	$I_O = 5 \text{ mA}$			0.25	V
VBSEL, $\overline{\text{CI}}$	and TE INPUTS					
V <sub>IL</sub>	Low-level input voltage		0		0.4	V
V <sub>IH</sub>	High-level input voltage		1.4			V
IIL	CE and TE low-level input current		-1			^
II <sub>H</sub>	CE and TE high-level input current				1	μΑ
I <sub>IL</sub>	VBSEL low-level input current	VBSEL = 0 (LOW)	-20			μΑ
I <sub>IH</sub>	VBSEL high-level input current	VBSEL = V <sub>CC</sub> (HI)			40	μΛ
TIMERS						
$t_{(PRECHG)}$	Precharge time		1,584	1,800	2,016	s
t <sub>(CHG)</sub>	Charge time		22,176	25,200	28,224	S
$I_{(FAULT)}$	Timer fault recovery current			200		μΑ
SLEEP CC	MPARATOR					
$V_{(SLP)}$	Sleep-mode entry threshold voltage	22777			≤ V <sub>I(OUT)</sub> + 80 mV	V
$V_{(SLPEXIT)}$	Sleep-mode exit threshold voltage	$2.3 \text{ V} \leq \text{V}_{\text{I(OUT)}} \leq \text{V}_{\text{O(REG)}}$	V <sub>CC</sub> ≥ V <sub>I(0</sub> + 190	OUT)		V
	Sleep-mode entry deglitch time	V <sub>(IN)</sub> decreasing below threshold, t <sub>FALL</sub> = 100 ns, 10-mV overdrive	250	375	500	ms
THERMAL	SHUTDOWN THRESHOLDS					
T <sub>(SHTDWN)</sub>	Thermal trip threshold			165		
,	Thermal hysteresis	T <sub>J</sub> increasing	15			°C
UNDERVO	LTAGE LOCKOUT				1	
UVLO	Undervoltage lockout	Decreasing V <sub>CC</sub>	2.4	2.5	2.6	٧
	Hysteresis			27		mV



### **PIN CONFIGURATION**

# DRC PACKAGE (TOP VIEW)

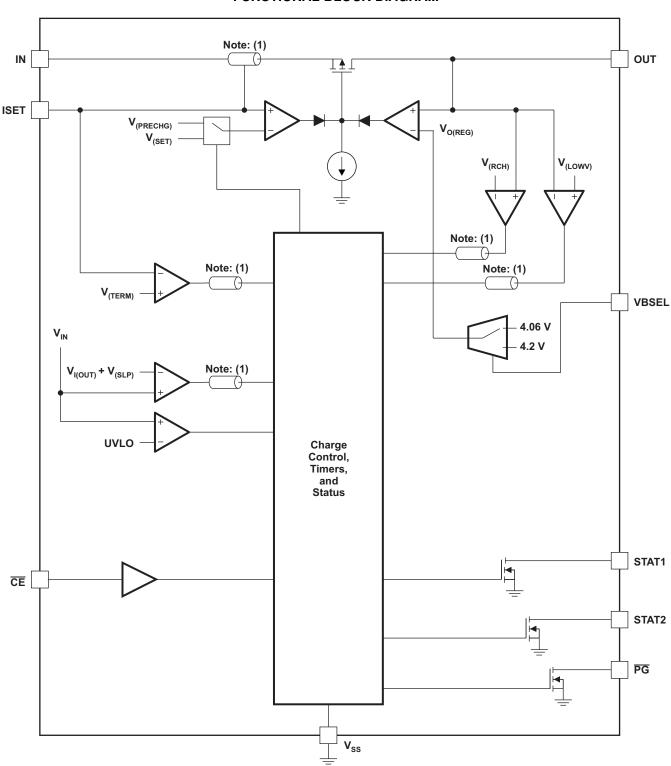


#### **TERMINAL FUNCTIONS**

TERMIN	MINAL I/O		DESCRIPTION
NAME	NO.		
CE	9	I	Charge enable input (active-low)
N.C.	2	_	No Connection. Leave this pin unconnected. Used for internal test purposes.
IN	1	I	Adapter dc voltage. Connect minimum 0.1-μF capacitor to V <sub>SS</sub> .
ISET	6	I	Charge current. External resistor to $V_{SS}$ sets precharge and fast-charge current, and also the termination current value. Can be used to monitor the charge current.
OUT	10	0	Charge current output. Connect minimum 0.1-μF capacitor to V <sub>SS</sub> .
PG	8	0	Power-good status output (open-drain)
STAT1	3	0	Charge status outputs (open drain)
STAT2	4	0	Charge status outputs (open-drain)
VBSEL	7	I	Voltage output selection. (HI = 4.06 V, LO = 4.2 V)
V <sub>SS</sub>	5	_	Ground
Thermal pad	_	_	There is an internal electrical connection between the exposed thermal pad and the VSS pin of the device. The exposed thermal pad must be connected to the same potential as the VSS pin on the printed-circuit board. <i>Do not use the thermal pad as the primary ground input for the device</i> . The VSS pin must be connected to ground at all times.



### **FUNCTIONAL BLOCK DIAGRAM**



(1) Signal deglitched



### TYPICAL CHARACTERISTICS

DROPOUT VOLTAGE **JUNCTION TEMPERATURE** 450  $I_{O(OUT)}$  = 1000 mA 400 350  $I_{O(OUT)} = 750 \text{ mA}$ Dropout Voltage - mV 300 250  $I_{O(OUT)} = 500 \text{ mA}$ 200 150  $I_{O(OUT)} = 250 \text{ mA}$ 100 50

50

100

T<sub>J</sub> - Junction Temperature - °C Figure 1.

150

0 L

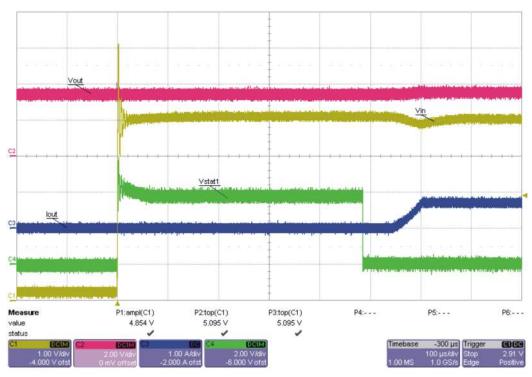


Figure 2. V<sub>IN</sub> Hot-Plug Power-Up Sequence

C001



# **TYPICAL CHARACTERISTICS (continued)**

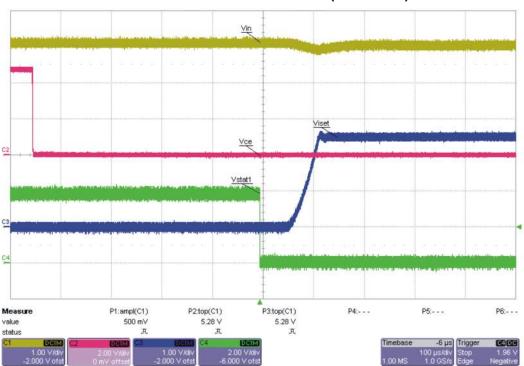


Figure 3. Charge Enable Power-Up Sequence ( $\overline{\text{CE}}$  = High-to-Low)

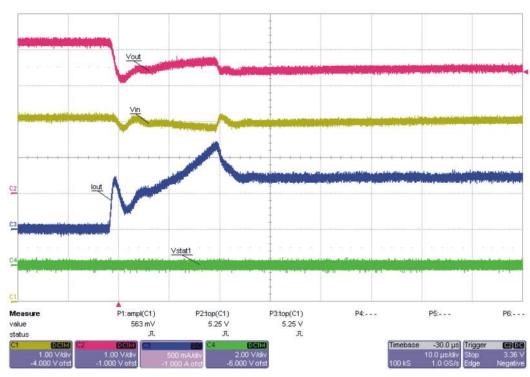


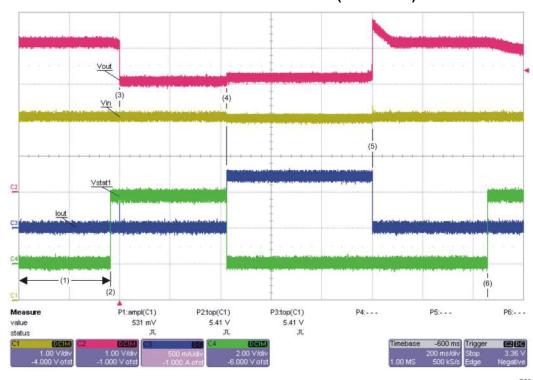
Figure 4. Battery Hot-Plug During Charging Phase

C003

C002



### **TYPICAL CHARACTERISTICS (continued)**



- (1) No battery In termination deglitch prior to STAT1 going high. V<sub>OUT</sub> (V<sub>BAT</sub>) cycling between *charge* and *done* prior to screen capture.
- (2) Stat1 goes high In done state
- (3) 2-V battery is inserted during the charge done state.
- (4) Charging is initiated STAT1 goes low and charge current is applied.
- (5) Battery is removed V<sub>OUT</sub> goes into regulation, I<sub>OUT</sub> goes to zero, and termination deglitch timer starts running (same as state 1).
- (6) Deglitch timer expires charge done is declared.

Figure 5. Battery Hot-Plug and Removal Power Sequence



### **FUNCTIONAL DESCRIPTION**

The device supports a precision Li-Ion, Li-Pol charging system suitable for single cells. Figure 6 shows a typical charge profile, and Figure 7 shows an operational flow chart.

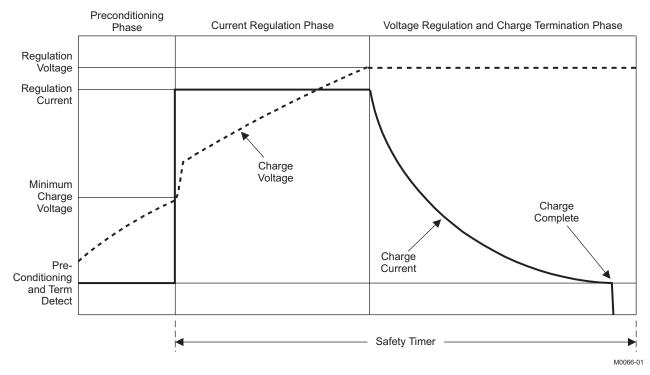


Figure 6. Typical Charging Profile



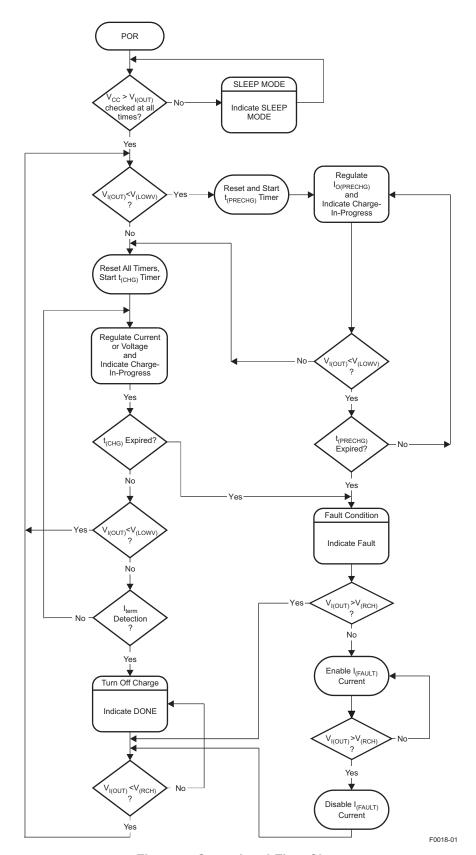


Figure 7. Operational Flow Chart



### **Battery Preconditioning**

During a charge cycle, if the battery voltage is below the  $V_{(LOWV)}$  threshold, the device applies a precharge current,  $I_{O(PRECHG)}$ , to the battery. This feature revives deeply discharged cells. Resistor  $R_{SET}$ , connected between the ISET and  $V_{SS}$ , determines the precharge rate. The  $V_{(PRECHG)}$  and  $K_{(SET)}$  parameters are specified in the *Electrical Characteristics* table.

$$I_{O(PRECHG)} = \frac{K_{(SET)} \times V_{(PRECHG)}}{R_{SET}}$$
(1)

The device activates a safety timer,  $t_{(PRECHG)}$ , during the conditioning phase. If the  $V_{(LOWV)}$  threshold is not reached within the timer period, the device turns off the charger and enunciates FAULT on the STATx pins. See the *Timer Fault Recovery* section for additional details.

#### **Battery Fast-Charge Constant Current**

The device offers on-chip current regulation with programmable set point. Resistor  $R_{SET}$ , connected between the ISET and  $V_{SS}$ , determines the charge rate. The  $V_{(SET)}$  and  $K_{(SET)}$  parameters are specified in the specifications table

$$I_{O(OUT)} = \frac{K_{(SET)} \times V_{(SET)}}{R_{SET}}$$
 (2)

### **Charge-Current Monitor**

When the charge function is enabled internal circuits generate a current proportional to the charge current at the ISET pin. This current, when applied to the external charge current programming resistor R<sub>ISET</sub> generates an analog voltage that can be monitored by an external host to calculate the current sourced from the OUT pin.

$$V(ISET) = I(OUT) \times \frac{R_{ISET}}{K_{(SET)}}$$
(3)

### **Battery Fast-Charge Voltage Regulation**

The voltage regulation feedback is through the OUT pin. This input is tied directly to the positive side of the battery pack. The device monitors the battery-pack voltage between the OUT and  $V_{SS}$  pins. When the battery voltage rises to the  $V_{O(REG)}$  threshold, the voltage regulation phase begins and the charging current begins to taper down.

As a safety backup, the device also monitors the charge time in the charge mode. If charge is not terminated within this time period,  $t_{(CHG)}$ , the charger is turned off and FAULT is set on the STATx pins. See the *Timer Fault and Recovery* section for additional details.

### **Charge Termination Detection and Recharge**

The device monitors the charging current during the voltage regulation phase. Once the termination threshold,  $I_{(TERM)}$ , is detected, charge is terminated. The  $V_{(TERM)}$  and  $K_{(SET)}$  parameters are specified in the specifications table.

$$I_{O(TERM)} = \frac{K_{(SET)} \times V_{(TERM)}}{R_{SET}}$$
(4)

After charge termination, the device restarts the charge once the voltage on the OUT pin falls below the  $V_{(RCH)}$  threshold. This feature keeps the battery at full capacity at all times.

The device monitors the charging current during the voltage regulation phase. Once the termination threshold,  $I_{(TERM)}$ , is detected, the charge is terminated immediately.

Resistor R<sub>SET</sub>, connected between the ISET and V<sub>SS</sub>, determines the current level at the termination threshold.

#### Sleep Mode

The device enters the low-power sleep mode if the input power (IN) is removed from the circuit. This feature prevents draining the battery during the absence of input supply.

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#### **Charge Status Outputs**

The open-drain STAT1 and STAT2 outputs indicate various charger operations as shown in the following table. These status pins can be used to drive LEDs or communicate to the host processor. Note that *OFF* indicates the open-drain transistor is turned off.

**Table 1. Status Pin Summary** 

CHANGE STATE	STAT1	STAT2		
Precharge in progress	ON	ON		
Fast charge in progress	ON	OFF		
Charge done	OFF	ON		
Charge suspend (temperature)				
Timer fault	OFF	OFF		
Sleep mode				

### **PG** Output

The open-drain power-good  $(\overline{PG})$  output <u>pulls</u> low when a valid input voltage is present. This output is turned off (high-impedance) in sleep mode. The  $\overline{PG}$  pin can be used to drive an LED or communicate to the host processor.

### Charge-Enabled (CE) Input

The  $\overline{\text{CE}}$  digital input is used to disable or enable the charge process. A low-level signal on this pin enables the charge and a high-level signal disables the charge and places the device in a low-power mode. A high-to-low transition on this pin also resets all timers and timer fault conditions.

### **Battery Voltage Selection, (VBSEL) Input**

The VBSEL input is used to select the output voltage of bq24083. A low level signal on this pin selects the charge voltage of 4.2 V. A high level voltage selects the charge voltage of 4.06 V. If VBSEL is left open, an internal current source flowdown ensures the charge voltage is set to 4.2 V (typical).

#### Timer Fault and Recovery

As shown in Figure 7, the device provides a recovery method to deal with timer fault conditions. The following summarizes this method:

#### **Condition Number 1**

OUT pin voltage is above the recharge threshold ( $V_{(RCH)}$ ), and a timeout fault occurs.

Recovery method: the device waits for the OUT pin voltage to fall below the recharge threshold. This could happen as a result of a load on the battery, self-discharge, or battery removal. Once the OUT pin voltage falls below the recharge threshold, the device clears the fault and starts a new charge cycle. A POR or CE toggle also clears the fault.

#### **Condition Number 2**

OUT pin voltage is below the recharge threshold (V<sub>(RCH)</sub>), and a timeout fault occurs

Recovery method: Under this scenario, the device applies the  $I_{(FAULT)}$  current. This small current is used to detect a battery removal condition and remains on as long as the battery voltage stays below the recharge threshold. If the OUT pin voltage goes above the recharge threshold, then the device disables the  $I_{(FAULT)}$  current and executes the recovery method described for condition number 1. Once the OUT pin voltage falls below the recharge threshold, the bq24083 clears the fault and starts a new charge cycle. A POR or  $\overline{CE}$  toggle also clears the fault.

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#### **APPLICATION INFORMATION**

### bq24083 CHARGER DESIGN EXAMPLE

#### Requirements

- Supply voltage = 5 V
- Fast-charge current of approximately 750 mA

#### **Calculations**

Program the charge current for 750 mA:

 $R_{ISET} = [V_{(SET)} \times K_{(SET)} / I_{(OUT)}]$ 

From electrical characteristics table,  $V_{(SET)} = 2.5 \text{ V}$ .

From electrical characteristics table,  $K_{(SFT)} = 322$ .

 $R_{ISFT} = [2.5 \text{ V} \times 322 / 0.75 \text{ A}] = 1.073 \text{ k}\Omega$ 

Selecting the closest standard value, use a 1.07-kΩ resistor connected between ISET (pin 6) and ground.

#### STAT Pins and PG Pin

Status pins Monitored by Processor:

Select a pullup resistor that can source more than the input bias (leakage) current of both the processor and status pins and still provide a logic high.  $R_{PULLUP} \leq [V_{(cc\text{-pullup})} - V_{(logic hi\text{-min})} / (I_{(P\text{-monitor})} + I_{(STAT\text{-}OpenDrain}))] = (3.3 \text{ V} - 1.9 \text{ V}) / (1 \mu\text{A} + 1 \mu\text{A}) \leq 700 \text{ k}\Omega$ ; Connect a 100-k $\Omega$  pullup between each status pin and the  $V_{CC}$  of the processor. Connect each status pin to a  $\mu\text{P}$  monitor pin.

Status viewed by LED:

Select an LED with a current rating less than 10 mA and select a resistor to place in series with the LED to limit the current to the desired current value (brightness).  $R_{LED} = [(V_{(IN)} - V_{(LED-on)}) / I_{(LED)}] = (5 V - 2 V) / 1.5 mA = 2 k\Omega$ . Place an LED and resistor in series between the input and each status pin.

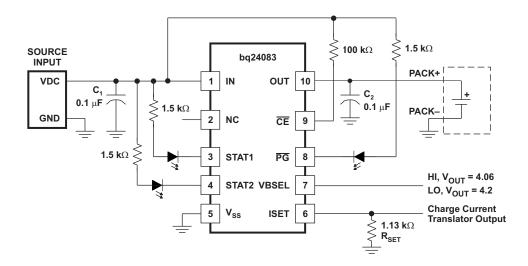
#### **Selecting Input and Output Capacitors**

In most applications, all that is needed is a high-frequency decoupling capacitor on the input power pin. A 0.1- $\mu$ F ceramic capacitor, placed in close proximity to the IN pin and GND pad works well. In some applications, it may be necessary to protect against a hot plug input voltage overshoot. This is done in three ways:

- 1. The best way is to add an input zener, 6.2 V, between the IN pin and VSS.
- 2. A low-power zener is adequate for the single event transient. Increasing the input capacitance lowers the characteristic impedance which makes the input resistance move effective at damping the overshoot, but risks damaging the input contacts by the high inrush current.
- 3. Placing a resistor in series with the input dampens the overshoot, but causes excess power dissipation.

The device only requires a small capacitor for loop stability. A 0.1- $\mu F$  ceramic capacitor placed between the OUT and GND pad is typically sufficient.





#### **Thermal Considerations**

The bq24083 is in a thermally enhanced MLP package. The package includes a thermal pad to provide an effective thermal contact between the device and the printed-circuit board (PCB). Full PCB design guidelines for this package are provided in the application report entitled, *QFN/SON PCB Attachment* (TI Literature Number SLUA271).

The most common measure of package thermal performance is thermal impedance ( $R_{\theta JA}$ ) measured (or modeled) from the device junction to the air surrounding the package surface (ambient). The mathematical expression for  $R_{\theta JA}$  is:

$$R_{\theta JA} = \frac{T_J - T_A}{P} \tag{5}$$

#### Where:

- T<sub>J</sub> = device junction temperature
- T<sub>A</sub> = ambient temperature
- P = device power dissipation

Factors that can greatly influence the measurement and calculation of R<sub>BJA</sub> include:

- Orientation of the device (horizontal or vertical)
- Volume of the ambient air surrounding the device under test and airflow
- Whether other surfaces are in close proximity to the device being tested
- Use multiple 10–13 mil vias in the PowerPAD™ to copper ground plane.
- Avoid cutting the ground plane with a signal trace near the power IC.
- The PCB must be sized to have adequate surface area for heat dissipation.
- FR4 (figerglass) thickness should be minimized.

The device power dissipation, P, is a function of the charge rate and the voltage drop across the internal Power FET. It can be calculated from the following equation:

$$P = (V_{(IN)} - V_{(OUT)}) \times I_{O(OUT)}$$
(6)

Due to the charge profile of Li-xx batteries, the maximum power dissipation is typically seen at the beginning of the charge cycle when the battery voltage is at its lowest. See Figure 6.



### **PCB Layout Considerations**

It is important to pay special attention to the PCB layout. The following provides some guidelines:

- To obtain optimal performance, the decoupling capacitor from V<sub>CC</sub> to V<sub>(IN)</sub> and the output filter capacitors from OUT to V<sub>SS</sub> should be placed as close as possible to the device, with short trace runs to both signal and V<sub>SS</sub> pins. The V<sub>SS</sub> pin should have short trace runs to the GND pin.
- All low-current V<sub>SS</sub> connections should be kept separate from the high-current charge or discharge paths from the battery. Use a single-point ground technique incorporating both the small-signal ground path and the power ground path.
- The high-current charge paths into IN and from the OUT pins must be sized appropriately for the maximum charge current in order to avoid voltage drops in these traces.
- The device is packaged in a thermally enhanced MLP package. The package includes a thermal pad to
  provide an effective thermal contact between the device and the printed circuit board (PCB). Full PCB design
  guidelines for this package are provided in the application report entitled, QFN/SON PCB Attachment
  (TI Literature Number SLUA271).

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#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
BQ24083DRCR	ACTIVE	VSON	DRC	10	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	CFZ	Samples
BQ24083DRCT	ACTIVE	VSON	DRC	10	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	CFZ	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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# **PACKAGE OPTION ADDENDUM**

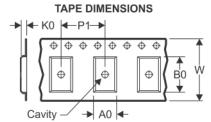
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# PACKAGE MATERIALS INFORMATION

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### TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

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Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
BQ24083DRCR	VSON	DRC	10	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
BQ24083DRCT	VSON	DRC	10	250	180.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2

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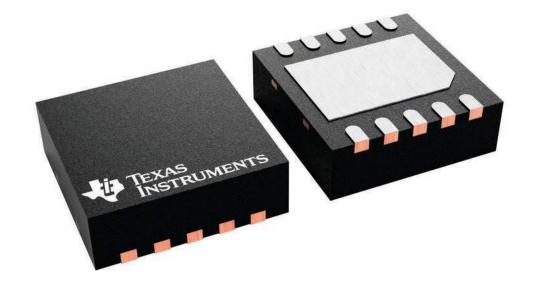
#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
BQ24083DRCR	VSON	DRC	10	3000	367.0	367.0	35.0
BQ24083DRCT	VSON	DRC	10	250	210.0	185.0	35.0

3 x 3, 0.5 mm pitch

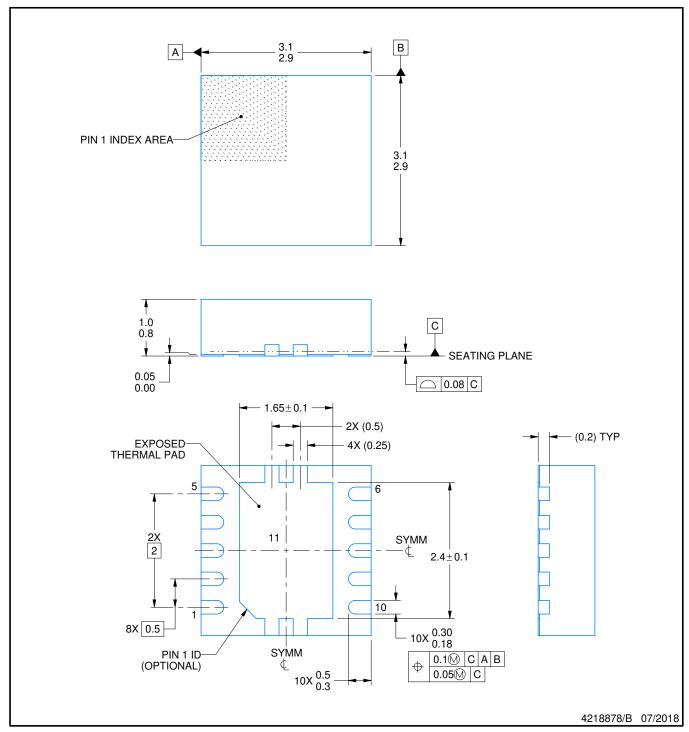
PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





PLASTIC SMALL OUTLINE - NO LEAD

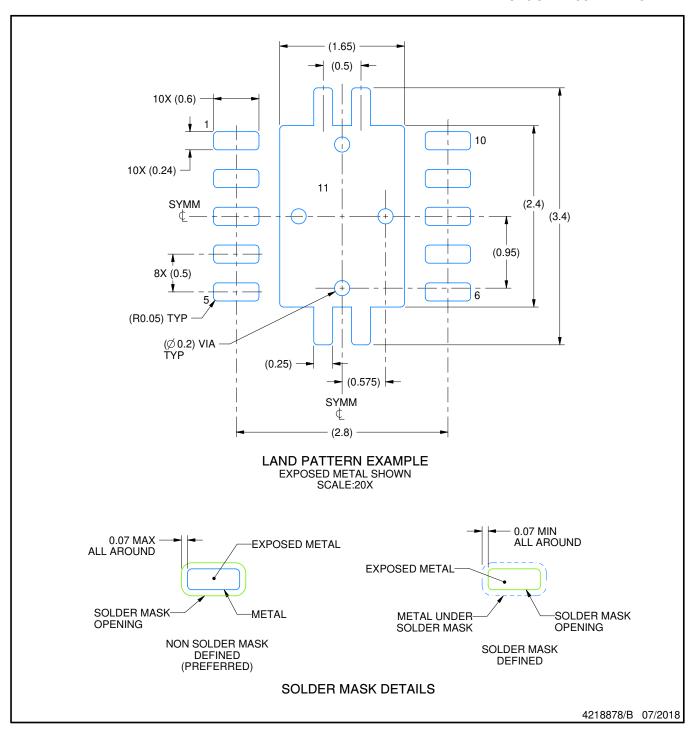


#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.



PLASTIC SMALL OUTLINE - NO LEAD

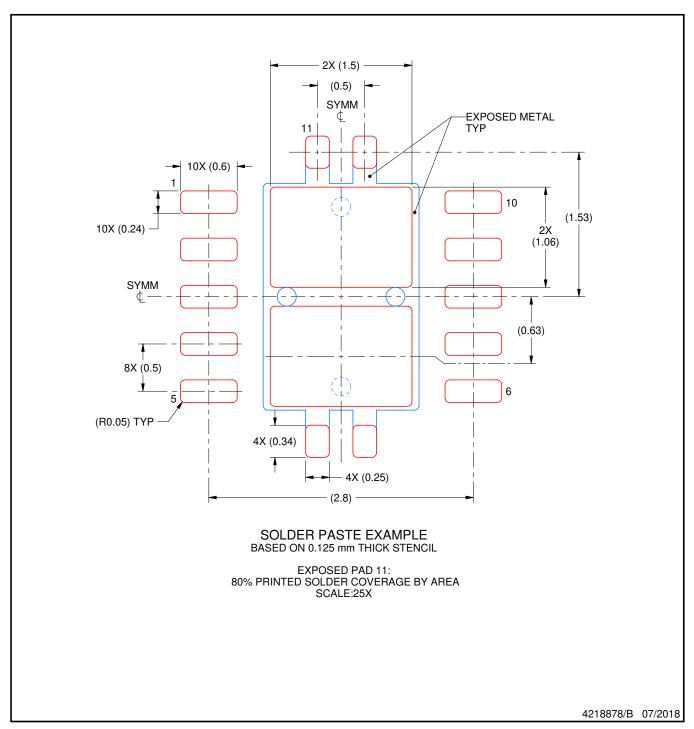


NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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